

METHOD OF FABRICATING A DIELECTRIC LAYER FOR A  
SEMICONDUCTOR STRUCTURE

ABSTRACT OF THE DISCLOSURE

Fabricating a semiconductor structure includes establishing a non-stoichiometry associated with a dielectric layer, where the degree of non-stoichiometry  
5 corresponds to a nitrogen profile of the dielectric layer. Deposition of the dielectric layer outwardly from a substrate is controlled to substantially yield the established non-stoichiometry of the dielectric layer. Nitrogen is incorporated into the dielectric layer to  
10 substantially yield the nitrogen profile without nitridation of the interface.